L Number	Hits	Search Text	DB	Time stamp
1	68	(island-like adj semiconductor\$2)same (base underl\$4 undercoat\$4)	USPAT;	2004/09/03 20:09
		(1.1.16.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.	US-PGPUB	2004/00/02 20 10
2	119	(island\$1like island adj like)near5 (base underl\$4 undercoat\$4)	USPAT; US-PGPUB	2004/09/03 20:19
3	74	((island\$1like island adj like)near5 (base underl\$4 undercoat\$4)) and	USPAT;	2004/09/03 20:15
	, , ,	(lcd electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon	US-PGPUB	2001/09/03 20:13
		adj2 insulator\$2 tft thin adj film adj transistor\$2)		
4	26	(aluminum near2 oxide "Al.sub.2O.sub.3" aluminum adj nitride adj oxide	USPAT;	2004/09/03 20:11
		"AlN.sub.xO.sub.1-x" nitride near2 aluminum "AlN.sub.x" AlSiON	US-PGPUB	
		LaSiON ((aluminum) near2 (rare adj earth)) AlSiON LaSiON boron		
		near2 nitride)and (((island\$1like island adj like)near5 (base underl\$4 undercoat\$4)) and (lcd electroluminescent display\$2 soi		
		silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj		
		transistor\$2))		
5	140	(island\$1like island adj like)and (base underl\$4 undercoat\$4)	EPO; JPO;	2004/09/03 20:14
			DERWENT	
6	11	((island\$1like island adj like)and (base underl\$4 undercoat\$4)) and	EPO; JPO;	2004/09/03 20:15
		(lcd electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj transistor\$2)	DERWENT	
7	2	(island\$1 like island adj like)near5 (aluminum near2 oxide	USPAT;	2004/09/03 20:23
′	-	"Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x"	US-PGPUB	200 1/05/05 20:25
		nitride near2 aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2		
		(rare adj earth)) AlSiON LaSiON boron near2 nitride)		
8	3	(island\$11ike island adj like)and (aluminum near2 oxide	EPO; JPO;	2004/09/03 20:21
		"Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x" nitride near2 aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2	DERWENT	
		(rare adj earth)) AlSiON LaSiON boron near2 nitride)		
9	95	(soi silicon\$1on\$1insulator\$2 silicon adj insulat\$4)and (island-like adj	USPAT;	2004/09/03 20:23
		semiconductor\$2)and (base underl\$4 undercoat\$4)	US-PGPUB	
10	1	(soi silicon\$1on\$1insulator\$2 silicon adj insulat\$4)and (island-like adj	EPO; JPO;	2004/09/03 20:23
		semiconductor\$2)and (base underl\$4 undercoat\$4)	DERWENT	2004/00/03 20 25
11	103	(((pattern\$4 etch\$4 taper tapering tapered)near5(aluminum near2 oxide	USPAT; US-PGPUB	2004/09/03 20:27
		"Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x" nitride near2 aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2	03-10108	
		(rare adj earth)) AlSiON LaSiON boron near2 nitride))near17(substrate		
		translucent plastic quartz glass))and (lcd electroluminescent display\$2		
		soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj		
.	C A	transistor\$2)	LICDAT.	2004/00/02 20-26
12	64	(((thick thicker thinner)near5(aluminum near2 oxide "Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x" nitride near2	USPAT; US-PGPUB	2004/09/03 20:26
		aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2 (rare adj	034 01 05	
		earth)) AlSiON LaSiON boron near2 nitride))near17(substrate translucent		
		plastic quartz glass))and (lcd electroluminescent display\$2 soi		
		silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj		
12	454	transistor\$2)	LICDATE.	2004/00/02 20:27
13	454	(((thick thicker thinner)near5(alumina ceramic))near17(substrate translucent plastic quartz glass))and (lcd electroluminescent display\$2	USPAT; US-PGPUB	2004/09/03 20:27
		soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj	05-1 01 01	
		transistor\$2)		
14	643	(((pattern\$4 etch\$4 taper tapering tapered)near5(alumina ceramic	USPAT;	2004/09/03 20:32
))near 17(substrate translucent plastic quartz glass))and (lcd	US-PGPUB	
		electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj transistor\$2)		
15	145	(((pattern\$4 etch\$4 taper tapering tapered)near5(alumina	USPAT;	2004/09/03 20:29
.	1-13))near17(substrate translucent plastic quartz glass))and (lcd	US-PGPUB	200 11 0 7/03 20.29
		electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon adj2		
		insulator\$2 tft thin adj film adj transistor\$2)		
16	134	(semiconductor with crystal crystalline single adj crystal)and ((((thick	USPAT;	2004/09/03 20:30
		thicker thinner)near5(alumina ceramic))near17(substrate translucent plastic quartz glass))and (lcd electroluminescent display\$2 soi	US-PGPUB	
		silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj		
		transistor\$2))	1	i

17	10	(((pattern\$4 etch\$4 taper tapering tapered)near5(aluminum near2 oxide	EPO; JPO;	2004/09/03 20:33
		"Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x"	DERWENT	
		nitride near2 aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2		
		(rare adj earth)) AlSiON LaSiON boron near2 nitride))and(substrate		
		translucent plastic quartz glass))and (lcd electroluminescent display\$2		
		soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj		
		transistor\$2)		